

F. Silicon and Group-IV Devices and Integration Technology 분과

2020년 2월 14일(금), 09:00-10:30 / Room B (에메랄드 II+III, 5층)

■ [FB1-F] Emerging Device Technology II

좌장: 김경록 교수 (UNIST), 신창환 교수 (성균관대학교)

FB1-F-1 09:00-09:30	[초청] Static Negative Capacitance nFETs with 1nm Effective Oxide Thickness Gate Stack Daewoong Kwon <i>Electrical Engineering, Inha University</i>
FB1-F-2 09:30-09:45	Sensitivity Analysis of NCFET-based 6-T SRAM Yuri Hong and Changhwan Shin <i>Department of Electrical and Computer Engineering, Sungkyunkwan University</i>
FB1-F-3 09:45-10:00	Precise Spectroscopic Analysis on Ultrathin Oxide Layer and Interfaces for Device Reliability Characterization Hyungtak Seo ^{1,2} , Hyunwoo Kang ² , and Shaid Iqbal ² <i>¹Department of Materials Science and Engineering, Ajou University, ²Department of Energy Systems Research, Ajou University</i>
FB1-F-4 10:00-10:15	Si Resonant Plasma-wave Transistor for Terahertz Detection Jong Yul Park, Min Woo Ryu, Sung-Ho Kim, and Kyung Rok Kim <i>School of Electrical and Computer Engineering, UNIST</i>
FB1-F-5 10:15-10:30	Impact of Bottom-Gate Biasing on Implant-free Junctionless Ge-on-Insulator n-MOSFETs Hyeong-Rak Lim ^{1,2,3} , Seong Kwang Kim ³ , Jae-Hoon Han ¹ , Hansung Kim ¹ , Dae-Myeong Geum ³ , Yun-Joong Lee ¹ , Young-Hun shin ¹ , Byeong-Kwon Ju ² , Hyung-Jun Kim ¹ , and Sanghyeon Kim ³ <i>¹KIST, ²School of Electrical Engineering, Korea University, ³School of Electrical Engineering, KAIST</i>